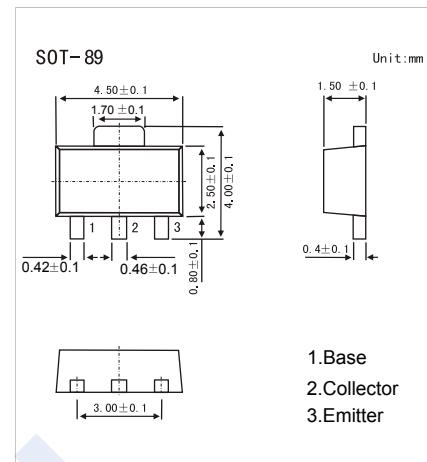


NPN Transistors**BF620 (KF620)****■ Features**

- Low current (max. 50mA)
- High voltage (max. 300V).
- Video output stages.

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	300	V
Collector - Emitter Voltage	V _{C EO}	300	
Emitter - Base Voltage	V _{EBO}	5	
Collector Current - Continuous	I _C	50	mA
Collector Power Dissipation	P _C	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C = 100 μA, I _E = 0	300			V
Collector-emitter breakdown voltage	V _{C EO}	I _C = 1 mA, I _B = 0	300			
Emitter-base breakdown voltage	V _{EBO}	I _E = 100 μA, I _C = 0	5			
Collector-base cut-off current	I _{CBO}	V _{CB} = 200 V, I _E = 0			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C = 0			50	
Collector-emitter saturation voltage	V _{C E(sat)}	I _C =30 mA, I _B =5mA			0.6	V
Base-emitter saturation voltage	V _{B E(sat)}	I _C =30 mA, I _B =5mA			1.2	
DC current gain	h _{FE}	V _{C E} = 20V, I _C = 25mA	50			
Transition frequency	f _T	V _{C E} = 10V, I _C = 10mA, f=100MHz	60			MHz

■ Marking

Marking	DC
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